FORM PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION				DOCKET NUMBER APPLICATION N 0629		P TO		
				APPLICANT Mark Albert Crowder				
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U.S. PATENT DOCUMENTS								
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS	FIL. DATE IF APPROP.	
SDF	6,177,301	01/23/01	Jung		438	150	05/13/99	
SDF	6,235,614	05/22/01	Yang		438	486	05/13/99	
SDE	6,274,888	08/14/01	Suzuki et al.		257	72	01/10/00	
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FOREIGN PATENT DOCUMENTS								
	DOCUMENT NUMBER	DATE	COUNTRY/NAME		CLASS	SUB CLASS	TRANSLATION YES NO	
	NOMBER	1	-			CLATOO	123	
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		1	<u> </u>					
OTHER DOCUMENTS								
SDE	Article entitled, "Phase Transformation Mechanisms involved in Excimer Laser crystallization of Amorphous Silicon Films", by Im et al., published in Appl. Phys. Lett. 63 (14), 4 October 1993, pp 1969-1971							
SOI	Article entitled, "Sequential Lateral Solidification of Thin Silicon Films on SiO ₂ ", by Sposili et al., published in Appl. Phys. Lett. 69 (19) 4 November 1996, pp 2864-2866							
SDI	Manipulation and (1998), pp 603-6	Article entitled, "Controlled Super-Lateral Growth of Si Films for Microstructural Manipulation and Optimization", by Im et al., published in Phys. Stat. Sol. (a) 166, 603 (1998), pp 603-617						
SOI	Displays", by In	Article entitled, "Crystalline Si Films for Integrated Active-Matrix Liquid-Crystal Displays", by Im et al., published in MRS Bulletin/ March 1996, pp 39-48						
SDA	Processed via Se Electron Device	Article entitled, "Low-Temperature Single-Crystal Si TFT's Fabricated on Si Films Processed via Sequential Lateral Solidification", by Crowder et al., published in IEEE Electron Device Letters, Vol. 19, No. 8, August 1998, pp 306-308						
SDT	•	Article entitled, "Single-Crystal Si Films for Thin-Film Transistor Devices", by Im et al., published in Appl. Phys. Lett. 70 (25), 23 June 1997, pp 34343436						
EXAMINER / Lander				DATE CONSIDERED 2/22/04				